ELECTRONICS, INC.
44 FARRAND STREET
BLOOMFIELD, NJ 07003
(973) 748–5089

NTE16001
Silicon NPN Transistor
Video IF Amp

Features:

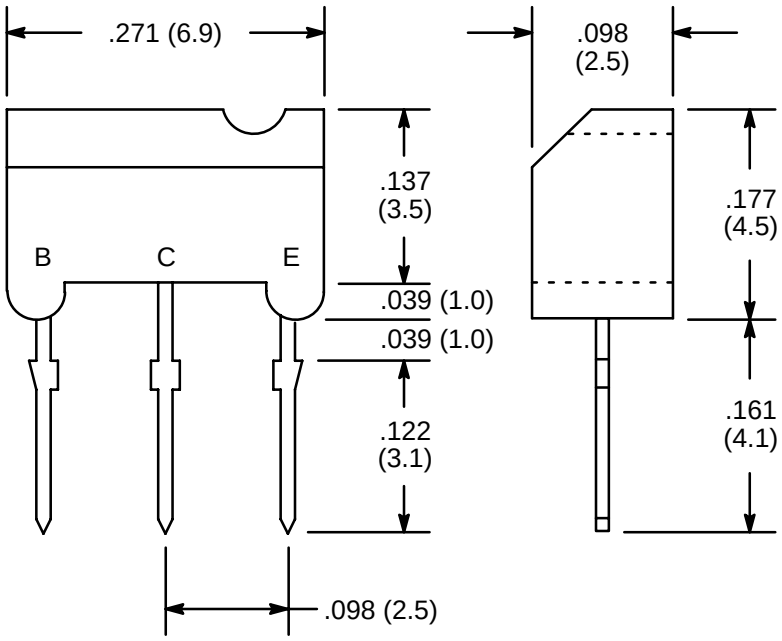
- High Transistion Frequency
- Good Linearity of DC Current Gain
- An M Type Mold package that Allows Easy Manual and Automatic Insertion. Can be Firmly Mounted Flush to PC Board Surface.

Absolute Maximum Ratings: (T_A = +25°C unless otherwise specified)

Collector–Base Voltage, V_{CBO} 45V
Collector–Emitter Voltage, V_{CEO} 35V
Emitter–Base Voltage, V_{EBO} 4V
Collector Current, I_C 50mA
Collector Power Dissipation, P_C 600mW
Operating Junction Temperature, T_J . . . . . +150°C
Storage Temperature Range, T_{stg} . . . . . –55° to +150°C

Electrical Characteristics: (T_A = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CEO}	V_{CE} = 20V, I_B = 0	–	–	10	μA
Collector–Base Voltage	V_{CBO}	I_C = 10μA, I_E = 0	45	–	–	V
Collector–Emitter Voltage	V_{CEO}	I_C = 1mA, I_B = 0	35	–	–	V
Emitter–Base Voltage	V_{EBO}	I_E = 10μA, I_C = 0	4	–	–	V
DC Current Gain	h_{FE}	V_{CB} = 10V, I_E = –10mA	20	50	100	
Collector–Emitter Saturation Volatge	$V_{CE(sat)}$	I_C = 20mA, I_B = 2mA	–	–	0.5	V
Transistion Frequency	f_T	V_{CB} = 10V, I_E = –10mA, f = 100MHz	300	500	–	MHz
Small–Signal Reverse Transfer Capacitance	C_{re}	V_{CE} = 10V, I_C = 1mA	–	–	1.5	pF
Power Gain	PG	V_{CB} = 10V, I_E = –10mA, f = 58MHz	–	18	–	dB


.271 (6.9)
.098
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.137
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B
C
E
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.161
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